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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









TN3019A



NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 500 mA and collector voltages up to 80 V. Sourced from Process 12.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	140	V
V_{EBO}	Emitter-Base Voltage	7.0	V
Ic	Collector Current - Continuous	1.0	Α
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

 $^{^{\}star}$ These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN3019A	
P _D	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

NPN General Purpose Amplifier (continued)

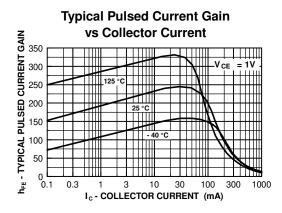
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 30 \text{ mA}, I_B = 0$	80		V
/ _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	140		V
/ _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	7.0		V
СВО	Collector-Cutoff Current	V _{CB} = 90 V, I _E = 0 V _{CB} = 90 V, I _E = 0, T _A = 150°C		0.01 10	μA μA
EBO	Emitter-Cutoff Current	$V_{CB} = 90 \text{ V}, I_{E} = 0, T_{A} = 150^{\circ}\text{C}$ $V_{EB} = 5.0 \text{ V}, I_{C} = 0$		0.01	μА
		$\begin{array}{l} I_{C}{=}150~\text{mA}, V_{CE}{=}10~\text{V}, T_{A}{=}{-}55^{\circ}\text{C} \\ I_{C} = 500~\text{mA}, ~V_{CE} = 10~\text{V*} \\ I_{C} = 1.0~\text{A}, ~V_{CE} = 10~\text{V*} \end{array}$	40 50 15		
				300	
			15		
√ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2 0.5	V
/ _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10 mA, I _B = 15 mA		1.1	V
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	I _C = 50 mA, V _{CE} = 10 V, f = 20 MHz	100		MHz
Cobo	Output Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		12	pF
Cibo	Input Capacitance	V _{BE} = 0.5 V, I _C = 0, f = 1.0 MHz		60	pF
n _{fe}	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz	80	400	
b'C _c	Collector Base Time Constant	$I_E = 10 \text{ mA}, V_{CB} = 10 \text{ V},$ f = 4.0 MHz		400	pS

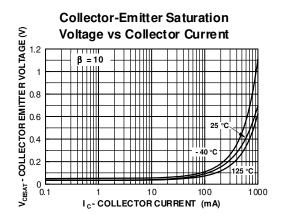
^{*}Pulse Test: Pulse Width $\leq\!300\,\mu\text{s},$ Duty Cycle $\leq\!1.0\%$

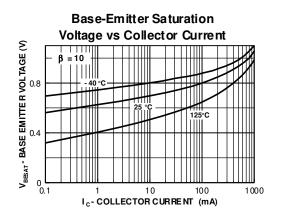
NPN General Purpose Amplifier

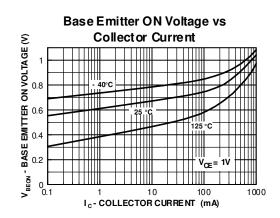
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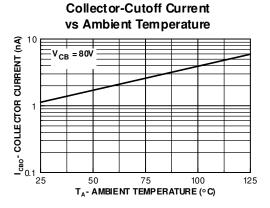
Typical Characteristics

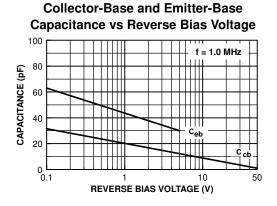










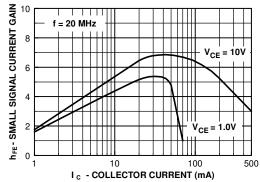


NPN General Purpose Amplifier

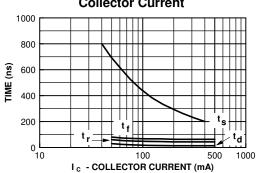
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Typical Characteristics (continued)

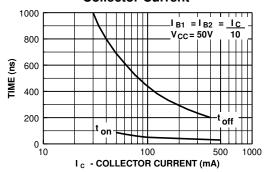




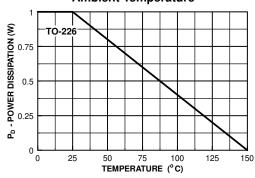
Switching Times vs Collector Current



Turn On and Turn Off Times vs Collector Current



Power Dissipation vs Ambient Temperature



NPN General Purpose Amplifier (continued)

Test Circuit

I _c	R _b	R _L
150 mA	314 Ω	330 Ω
200 mA	157 Ω	167 Ω
500 mA	94 Ω	100 Ω

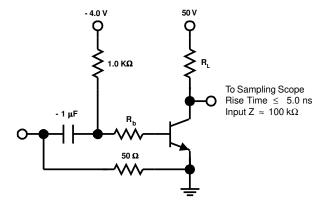
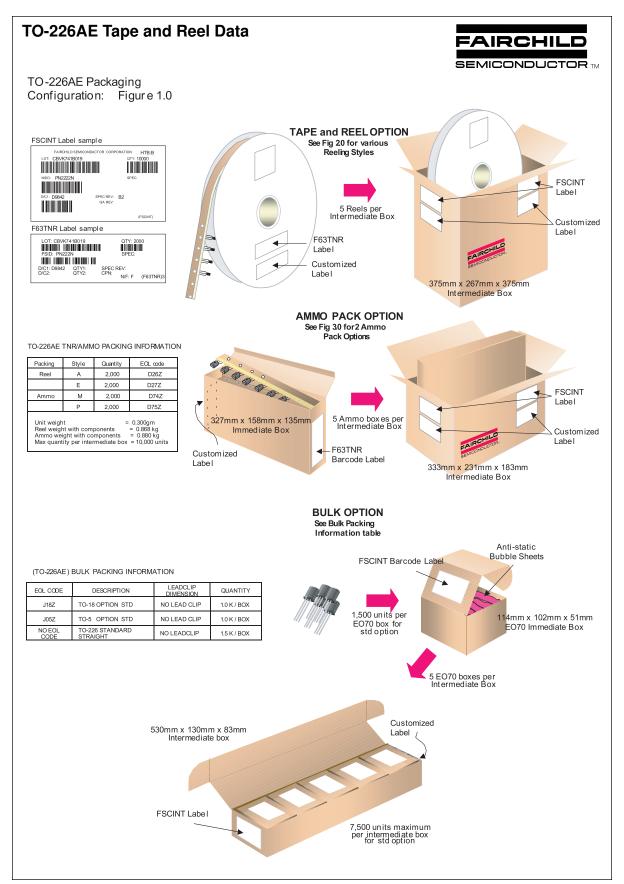




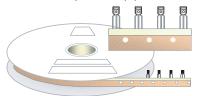
FIGURE 1: t_{ON} , t_{OFF} Test Circuit



TO-226AE Tape and Reel Data, continued

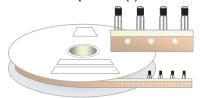
TO-226AE Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A" D26Z, D70Z (s/h)

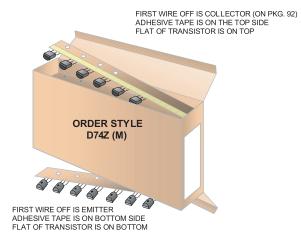
Machine Option "E"(J)



Style "E" D27Z, D71Z (s/h)

TO-226AE Radial Ammo Packaging

Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM



FLAT OF TRANSISTOR IS ON TOP

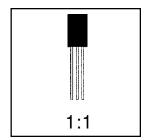
TO-226AE Tape and Reel Data, continued TO-226AE Tape and Reel Taping Dimension Configuration: Figure 4.0 ITEM DESCRIPTION SYMBOL DIMENSION Base of Package to Lead Bend 0.098 (max) Component Height Hb 1.078 (+/- 0.050) User Direction of Feed 0.630 (+/- 0.020) Lead Clinch Height НΩ Component Base Height H1 0.748 (+/- 0.020) Component Alignment (side/side) Pd 0.040 (max) 0.031 (max) Component Alignment (front/back) Hd 0.500 (+/- 0.020) Component Pitch РО Feed Hole Pitch 0.500 (+/- 0.008) Hole Center to First Lead P1 0.150 (+0.009, -0.010) Hole Center to Component Center P2 0.247 (+/- 0.007) Lead Spread F1/F2 0.104 (+/- 0 010) Lead Thickness d 0.018 (+0.002, -0.003) 0.429 (max) Out Lead Length Taped Lead Length L1 0.209 (+0.051, -0.052) Taped Lead Thickness 0.032 (+/- 0.006) Carrier Tape Thickness t1 0.021 (+/- 0.006) TO-226AE Reel Carrier Tape Width 0.708 (+0.020, -0.019) W Configuration: Figure 5.0 Hold - down Tape Width wo 0.236 (+/- 0.012) 0.035 (max) Hold - down Tape position W1 0.360 (+/- 0.025) Feed Hole Position W2 0.157 (+0.008, -0.007) Sprocket Hole Diameter DO 0.004 (max) Lead Spring Out S Note: All dmensions are in inches. D4 ITEM DESCRIPTION SYMBOL MINIMUM MAXIMUM D2 Red Diameter 13975 14025 Arbor Hole Diameter (Standard) 1.200 D2 1.160 D2 0.650 0.700 (Small Hole) Core Diameter D3 3.100 3.300 Hub Recess Inner Diameter D4 3.100 Hub Recess Depth W 1 0.370 0.570 Range to Range Inner Width W2 1.630 1.690 Hub to Hub Center Width 2.090 WЗ Note: All dimensions are inches

TO-226AE Package Dimensions



TO-226AE (FS PKG Code 95, 99)



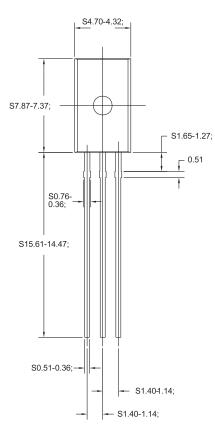


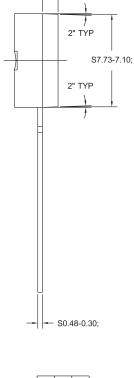
Scale 1:1 on letter size paper

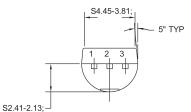
Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.300

- S1.52-1.02;









For leadformed option ordering, refer to Tape & Reel data information.

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